

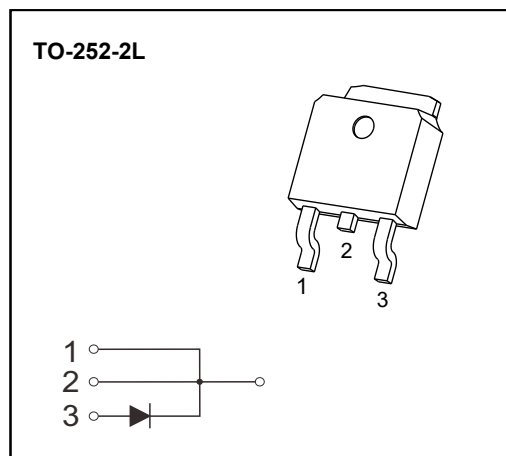
SiC Schottky Diode

Features

- Reverse withstand voltage 650V
- Zero reverse recovery current
- High working frequency
- Switch characteristics are not affected by temperature
- Fast switching speed
- Positive temperature coefficient of positive pressure drop

Advantages

- Very low switching loss
- Higher efficiency
- Low dependence of the system on the heat sink
- No thermal collapse in parallel devices



Application

- Switching mode power supply, AC/DC converter
- Power factor correction
- Motor drive
- PV inverter and wind turbine

Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Test conditions	Value	Unit
Peak repetitive reverse voltage	V_{RRM}		650	V
Working Peak Reverse voltage	V_{RWM}		650	V
DC Blocking Voltage	V_{DC}		650	V
Average rectified output current	$I_{F(AV)}$	Ta=25°C Ta=125°C Ta=150°C	30 14 8	A
Forward repetitive peak current	I_{FRM}	T _C =25°C, tp=10ms, Half Sine Wave T _C =110°C, tp=10ms, Half Sine Wave	45 21.5	A
Forward surge current	I_{FSM}	T _C =25°C, tp=10ms, Half Sine Wave T _C =110°C, tp=10ms, Half Sine Wave	72 55	A
Power dissipation	P_{tot}	Ta=25°C Ta=110°C	90 38	W
Junction temperature	T_j		-55 ~ +175	°C
Storage temperature	T_{stg}		-55 ~ +175	°C

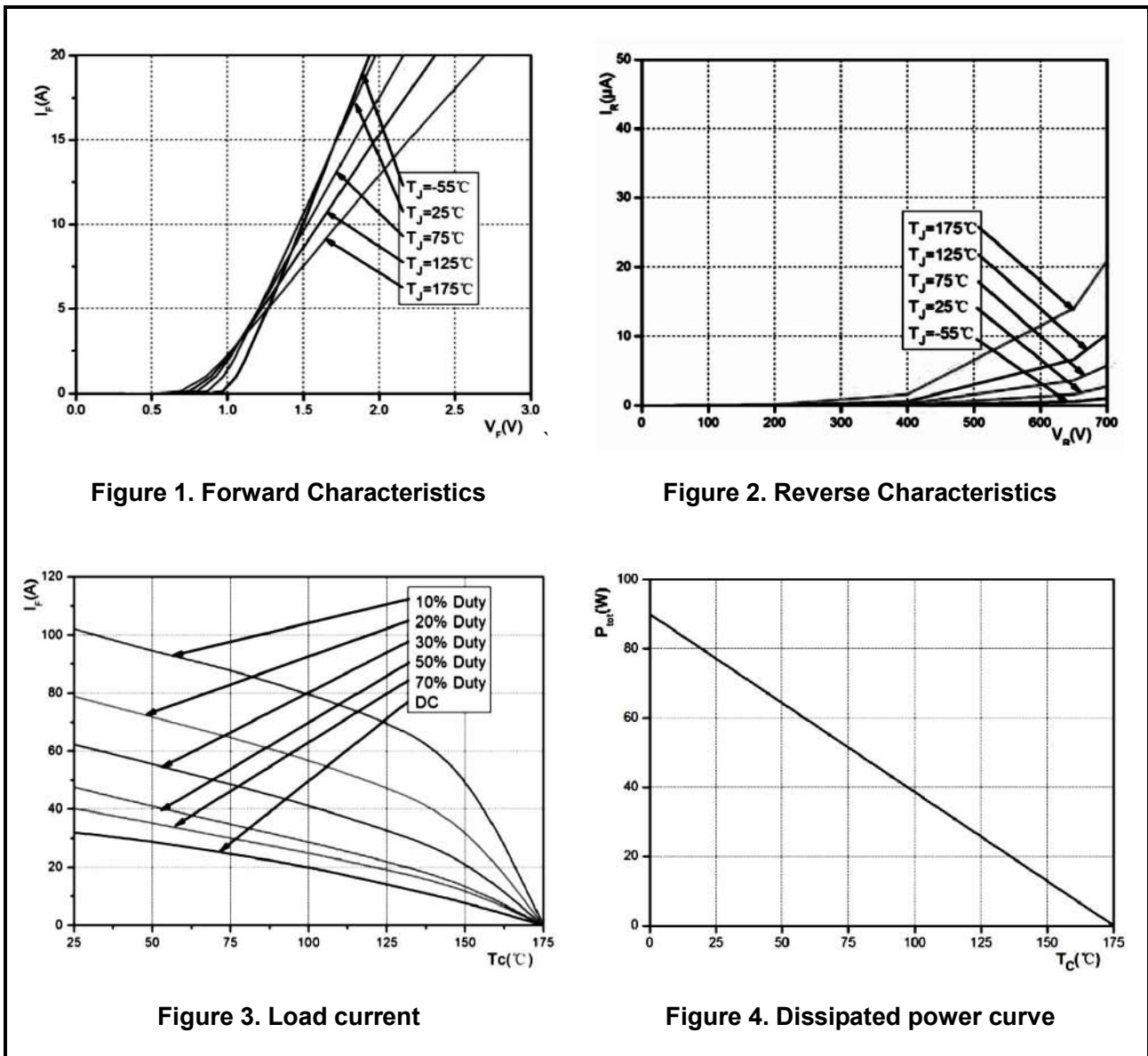
Thermal characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	2.3	°C/W

Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 8\text{ A}, T_J = 25^\circ\text{C}$ $I_F = 8\text{ A}, T_J = 175^\circ\text{C}$		1.4 1.57	1.8 2.4	V
Reverse current	I_R	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$ $V_R = 650\text{V}, T_J = 175^\circ\text{C}$		1 15	20 200	μA
Total capacitive charge	Q_C	$V_R = 400\text{V}, I_F = 8\text{ A}$ $di/dt = 500\text{A}/\mu\text{s}, T_J = 25^\circ\text{C}$		11		nC
Total capacitance	C	$V_R = 0\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ $V_R = 200\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ $V_R = 400\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$		580 58 42		pF

Typical Characteristics



Typical Characteristics

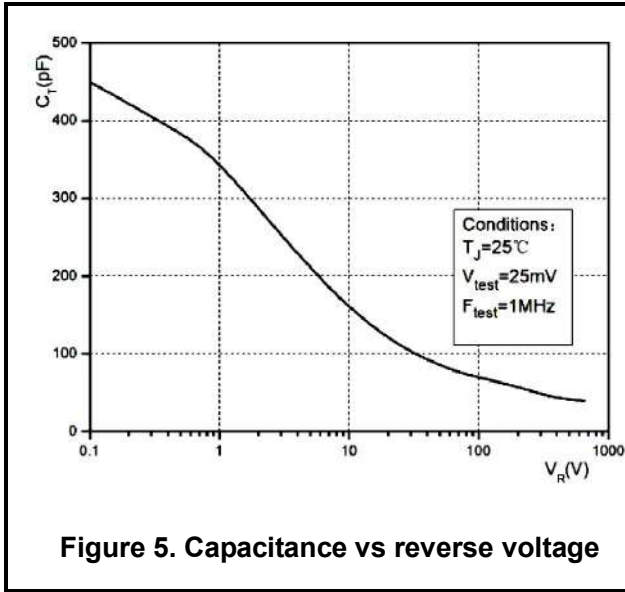


Figure 5. Capacitance vs reverse voltage

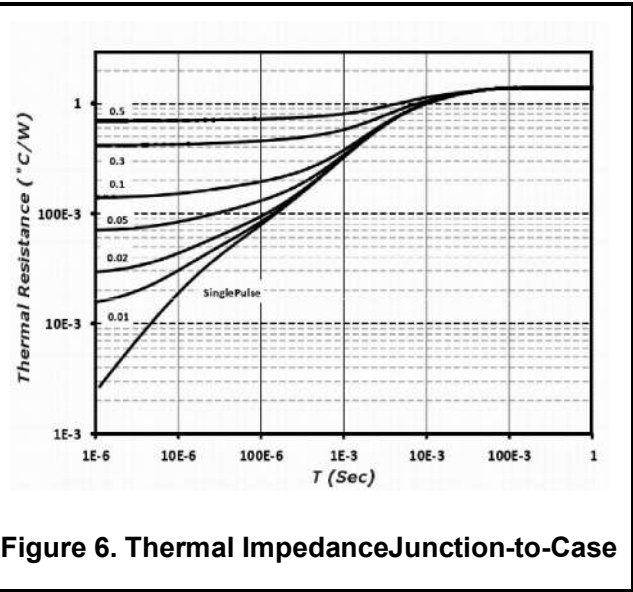
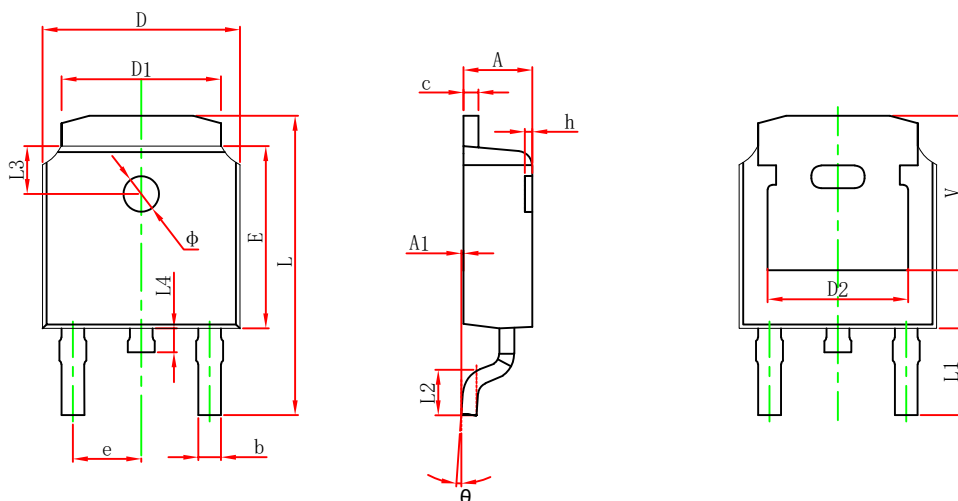


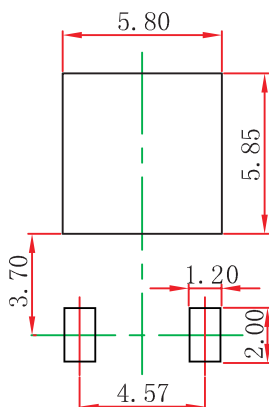
Figure 6. Thermal Impedance Junction-to-Case

TO- 252-2L Package Outline Dimensions



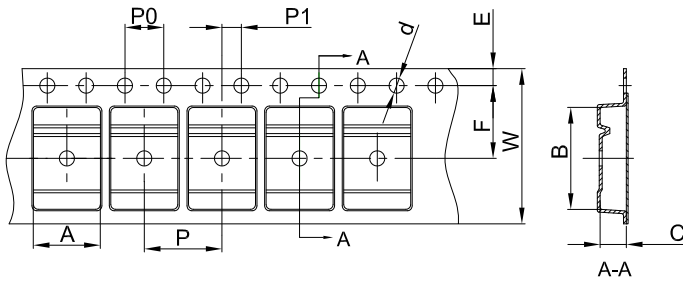
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



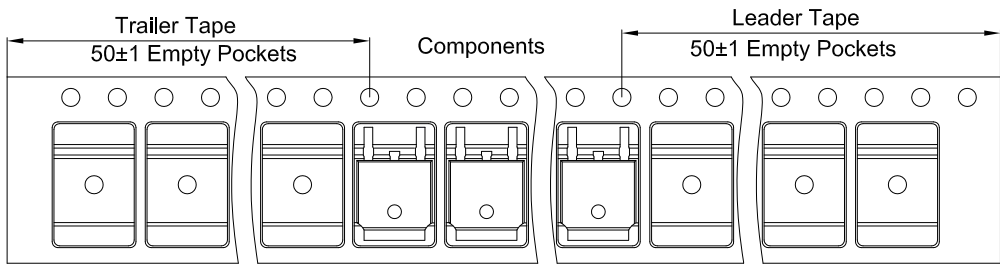
- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

TO-252 Embossed Carrier Tape

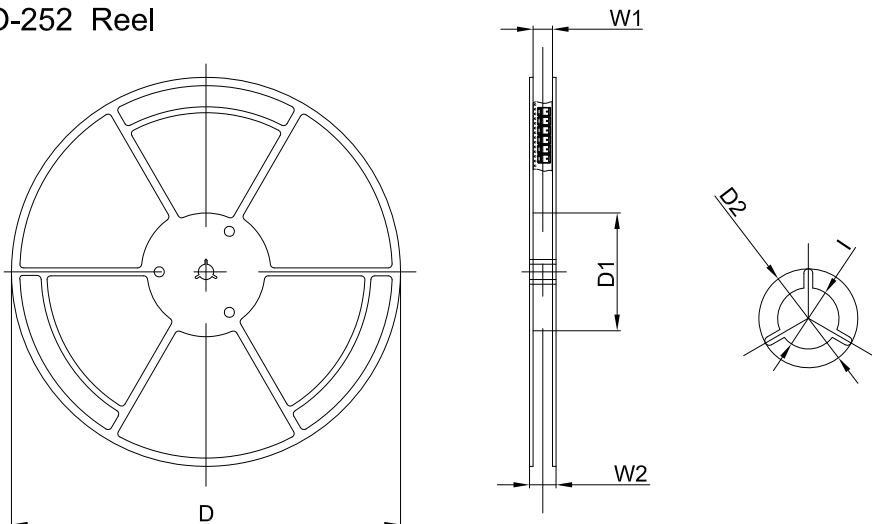


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13" Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	